

REMARKS

Favorable consideration of the present application, as now amended, is respectfully requested.

In accordance with 37 C.F.R. §1.173(c), the following is a statement of the status of the patent claims, and an explanation of the support in the disclosure of the patent for the changes made to the claims.

New claims 22-25 are being introduced. Claims 1-25 are present in the reissue patent application. Basis in the specification for the new claims 22-25 is found in the non-limiting exemplary embodiments, as set forth below:

22. A method of forming a cantilever probe contactor, the method comprising:

successively patterning a first and second sacrificial layer of resist over a substrate, each layer of resist having an opening;

First sacrificial layer 26 and second sacrificial layer 27-28.

depositing a first conductive material after patterning the first sacrificial layer,

Conductive member 9A.

depositing a second conductive material after patterning the second sacrificial layer to form a cantilever element having:

Member 7-8.

a first portion formed in an opening in the first sacrificial layer, and

Member 9A.

a second portion comprising a support element coupled to the first portion and formed in an opening in the second sacrificial layer; and

Layers 7-8.

removing the first and second sacrificial layers simultaneously.

Col. 8, lines 17-19.

23. A method of forming a cantilever probe contactor, the method comprising:

successively patterning a first and second sacrificial layer of resist over a substrate, each layer of resist having an opening;

First sacrificial layer 26 and second sacrificial layer 27-28.

depositing a first conductive material after patterning the first sacrificial layer;

Conductive member 9A.

depositing a second conductive material after patterning the second sacrificial layer to form a cantilever element having:

Member 7-8.

a first portion formed in an opening in the first sacrificial layer,

Member 9A.

a second portion comprising a support element coupled to the first portion and formed in an opening in the second sacrificial layer, and

Layers 7-8.

a third portion comprising a contact element coupled to the first portion, at least a part of the third portion being formed in the substrate; and

Member 9B.

removing the first and second sacrificial layers simultaneously,

Col. 8, lines 17-19.

wherein the contact element is formed of a conductive material in a predetermined opening formed in the substrate.

Col. 7, lines 8-12.

24. The method of claim 23, wherein the substrate is a silicon substrate.

Col. 6, lines 55-58.

25. The method of claim 22, wherein the conductive material includes at least nickel.

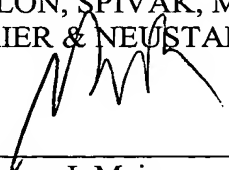
Col. 7, lines 42-46.

Patent No. 6,344,752
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248255US2 RE
Page 6

An early and favorable action on merits is therefore respectfully solicited.

Respectfully submitted,

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